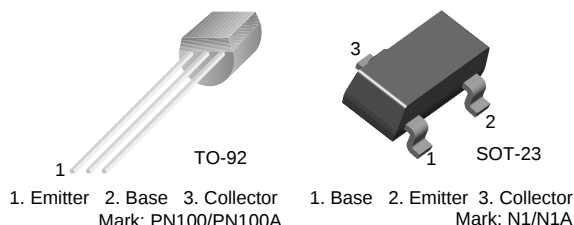


PN100/PN100A/MMBT100/MMBT100A

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300mA.
- Sourced from process 10.



Absolute Maximum Ratings* $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector current - Continuous	500	mA
T_J, T_{stg}	Junction and Storage Temperature	-55 ~ +150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 1\text{mA}, I_B = 0$	45		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector-Base Cutoff Current	$V_{CB} = 60\text{V}$		50	nA
I_{CES}	Collector-Emiitter Cutoff Current	$V_{CE} = 40\text{V}$		50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4\text{V}$		50	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}^*$ $I_C = 150\text{mA}, V_{CE} = 5.0\text{V}^*$	100 100 100 100	80 240 300 350	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.2 0.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.85 1.0	V V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$V_{CE} = 20\text{V}, I_C = 20\text{mA}$	250		MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}$		4.5	pF
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 5.0\text{V}$ $R_G = 2.0\text{k}\Omega, f = 1.0\text{KHz}$	100 100A	5.0 4.0	dB dB

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Thermal Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Max.		Units
		PN100 PN100A	*MMBT100 *MMBT100A	
P_D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/ $^{\circ}\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	$^{\circ}\text{C/W}$

* Device mounted on FR-4 PCB $1.6'' \times 1.6'' \times 0.06''$

Typical Characteristics

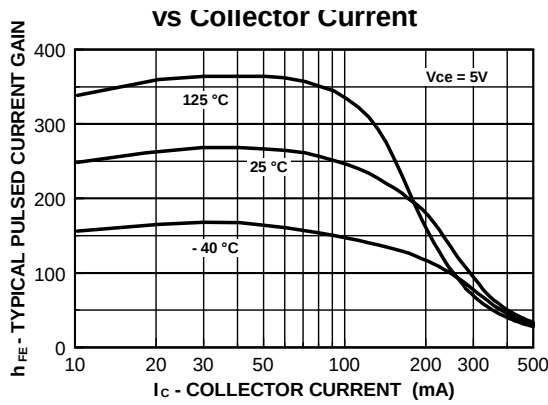


Figure 1. Typical Pulsed Current Gain vs Collector Current

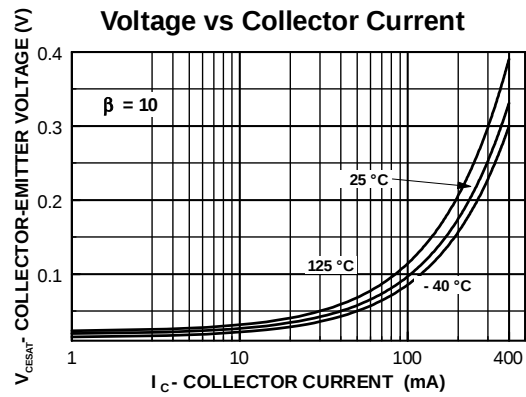


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

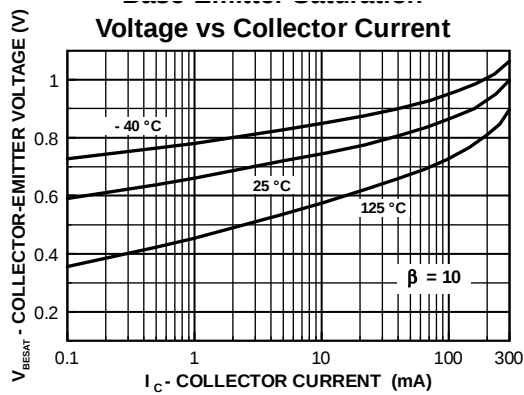


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

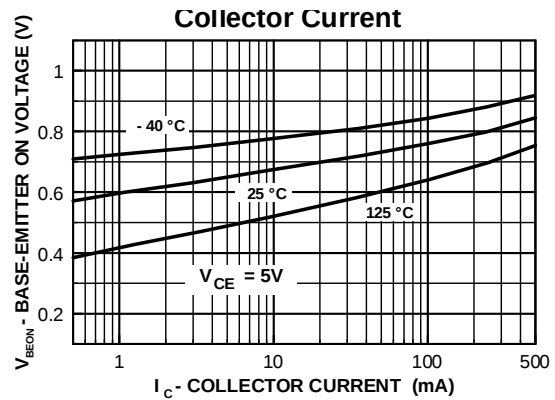


Figure 4. Base-Emitter On Voltage vs Collector Current

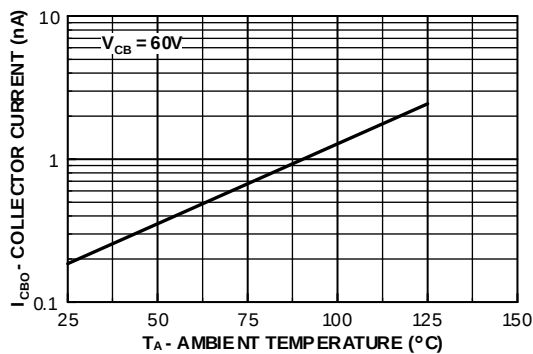


Figure 5. Collector Cutoff Current vs Ambient Temperature

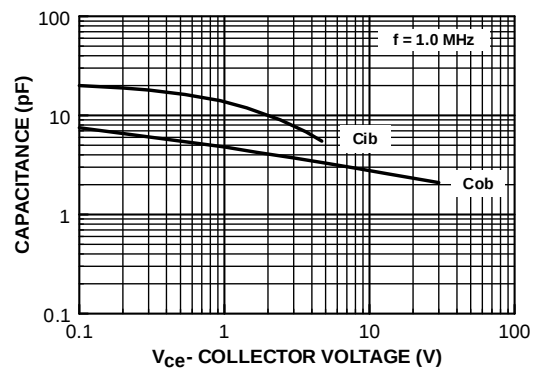


Figure 6. Input and Output Capacitance vs Reverse Voltag

Typical Characteristics (Continued)

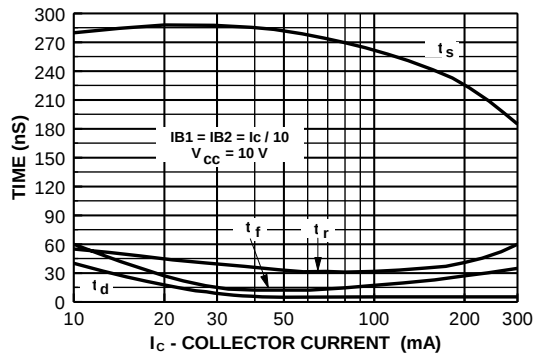


Figure 7. Switching Times vs Collector Current

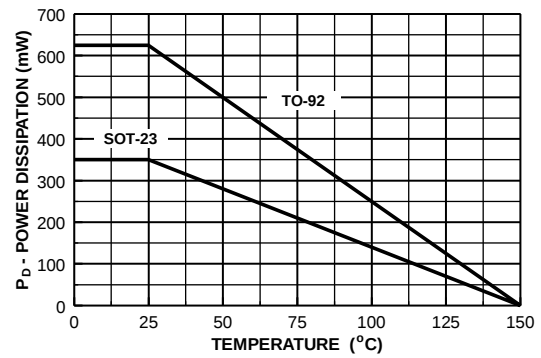
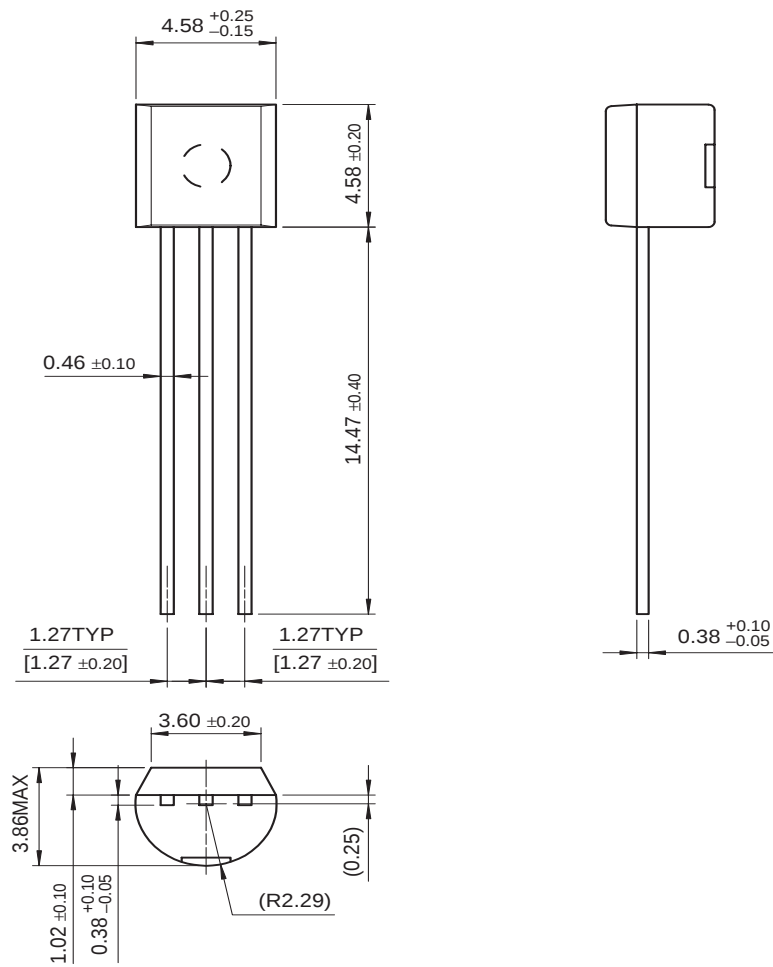


Figure 8. Power Dissipation vs Ambient Temperature

Package Dimensions

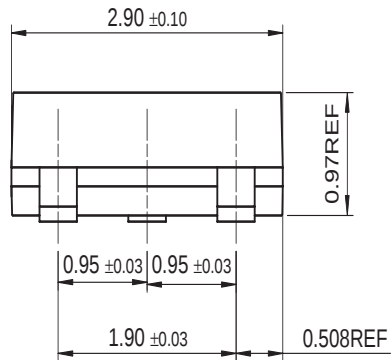
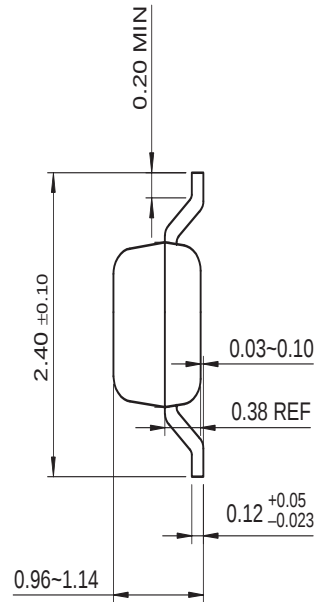
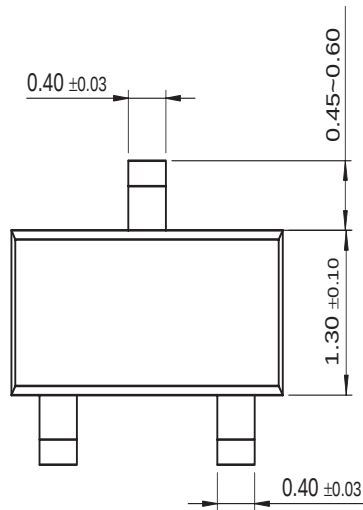
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Dimensions in Millimeters

Package Dimensions (Continued)

SOT-23



Dimensions in Millimeters

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	MSXPro™	RapidConnect™	TINYOPTO™	
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